

B<sup>1</sup>  
--U.S. Patent No. 5,415,835 shows a procedure of forming a fine pattern with a dual-beam interference exposure process. With this dual-beam interference exposure process, a pattern of 0.15 micron or less can be produced on a wafer.--

Please substitute the following paragraph for the paragraph starting at page 9, line 23 and ending at page 9, line 27. A marked-up copy of this paragraph, showing the changes made thereto is attached.

B<sup>2</sup>  
--In a fourth form of exposure method according to the present invention, one and the same mask pattern is projected onto a common exposure region in accordance with bright-field oblique illumination and bright-field perpendicular illumination.--

Please substitute the following paragraph for the paragraph starting at page 11, line 7 and ending at page 11, line 12. A marked-up copy of this paragraph, showing the changes made thereto is attached.

B<sup>3</sup>  
--In a fourth form of exposure apparatus according to the present invention, there is an exposure mode in which one and the same mask pattern is projected onto a common exposure region in accordance with bright-field oblique illumination and bright field perpendicular illumination.--